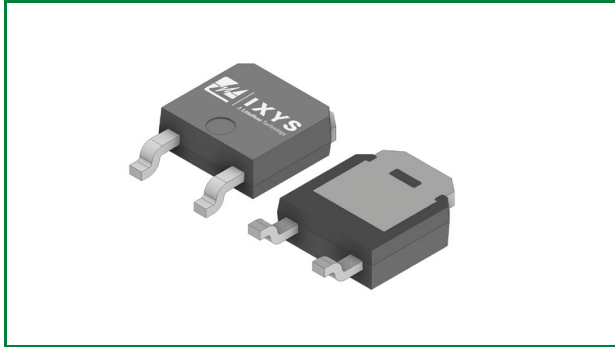


LSIC2SD120C10A  
1200 V, 10 A SiC Schottky Barrier Diode

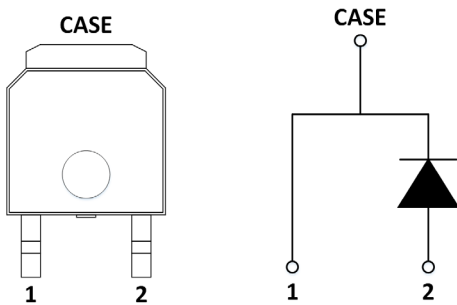


### Agency Approvals and Environmental

Environmental Approvals



### Pinout Diagram



### Product Summary

Characteristic	Value	Unit
$V_{RRM}$	1200	V
$I_F (T_C \le 135^\circ\text{C})$	15	A
$Q_C (V_R: 0-800\text{ V})$	56	nC

### Features

- AEC-Q101 Qualified
- MSL 1 Rated
- Positive temperature coefficient for safe operation and ease of paralleling
- 175 °C maximum operating junction temperature
- Excellent surge capability
- Extremely fast, temperature-independent switching behavior
- Dramatically reduced switching losses compared to Si bipolar diodes
- RoHS compliant, lead-free, and halogen-free

### Applications

- Boost diodes in PFC or DC/DC stages
- Switch-mode power supplies
- Solar inverters
- Uninterruptable power supplies
- Industrial motor drives
- Battery Chargers
- High speed rectifier

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## 1. Maximum Ratings

Characteristic	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	-	1200	V
DC Blocking Voltage	$V_R$	-	1200	V
Continuous Forward Current	$I_F$	$T_C = 25\text{ }^\circ\text{C}$	32	A
		$T_C = 135\text{ }^\circ\text{C}$	15	
		$T_C = 154\text{ }^\circ\text{C}$	10	
Non-repetitive Forward Surge Current	$I_{FSM}$	$T_C = 25\text{ }^\circ\text{C}$ , $t_p = 10\text{ ms}$ , Half sine pulse	80	A
$I^2t$	$\int I^2 dt$	$T_C = 25\text{ }^\circ\text{C}$ , $t_p = 10\text{ ms}$ , Half sine pulse	32	A <sup>2</sup> s
Power Dissipation	$P_{Tot}$	$T_C = 25\text{ }^\circ\text{C}$	150	W
		$T_C = 110\text{ }^\circ\text{C}$	65	
Operating Junction Temperature	$T_J$	-	-55 to 175	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-	-55 to 150	$^\circ\text{C}$
Lead Temperature for Soldering (MSL 1 Rated)	$T_{SOLD}$	-	260	$^\circ\text{C}$

## 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, junction-to-case	$R_{thJC,MAX}$	1.0	$^\circ\text{C}/\text{W}$

## 3. Electrical Characteristics

Characteristic	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Forward Voltage	$V_F$	$I_F = 10\text{ A}$ , $T_J = 25\text{ }^\circ\text{C}$	-	1.5	1.8	V
		$I_F = 10\text{ A}$ , $T_J = 175\text{ }^\circ\text{C}$	-	2.0	-	
Reverse Current	$I_R$	$V_R = 1200\text{ V}$ , $T_J = 25\text{ }^\circ\text{C}$	-	<1	100	$\mu\text{A}$
		$V_R = 1200\text{ V}$ , $T_J = 175\text{ }^\circ\text{C}$	-	4	-	
Total Capacitance	C	$V_R = 1\text{ V}$ , $f = 1\text{ MHz}$	-	580	-	pF
		$V_R = 400\text{ V}$ , $f = 1\text{ MHz}$	-	53	-	
		$V_R = 800\text{ V}$ , $f = 1\text{ MHz}$	-	40	-	
Total Capacitive Charge	$Q_C$	$V_R = 800\text{ V}$ , $Q_C = \int C(V) dV$	-	56	-	nC
Capacitance Stored Energy	$E_C$	$V_R = 800\text{ V}$	-	12.8	-	$\mu\text{J}$

4. Performance Curves

Figure 1. Typical Forward Characteristics

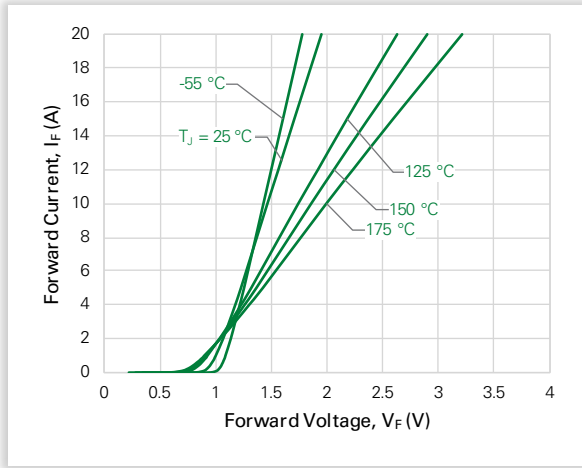


Figure 2. Typical Reverse Characteristics

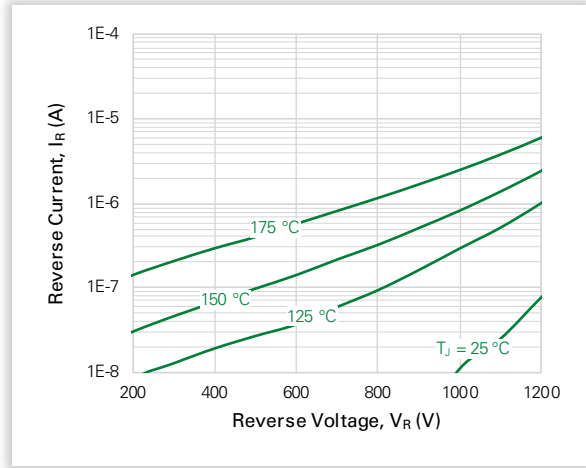


Figure 3. Power Derating

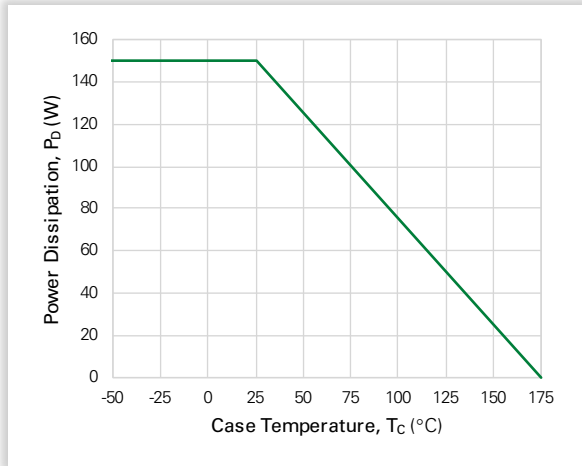


Figure 4. Current Derating

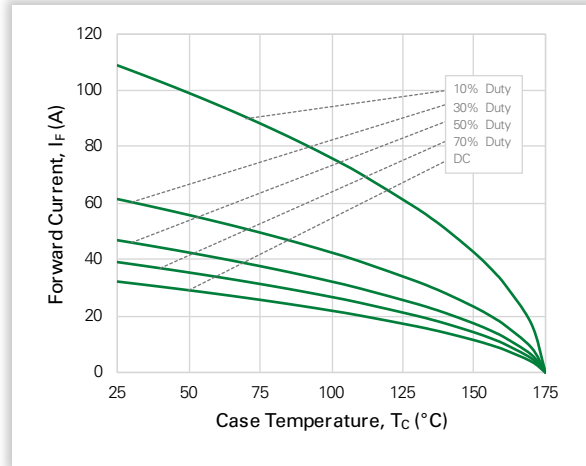


Figure 5. Capacitance vs. Reverse Voltage

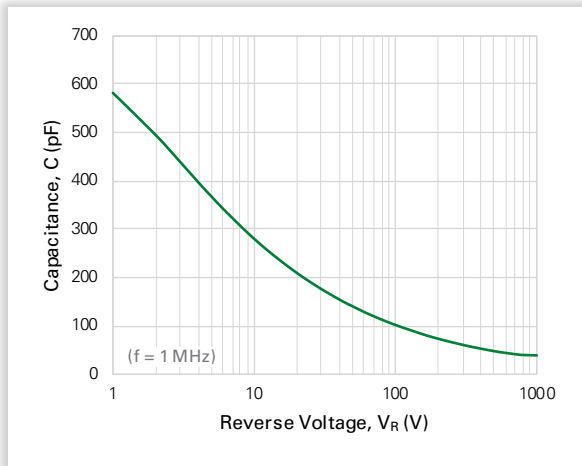


Figure 6. Capacitive Charge vs. Reverse Voltage

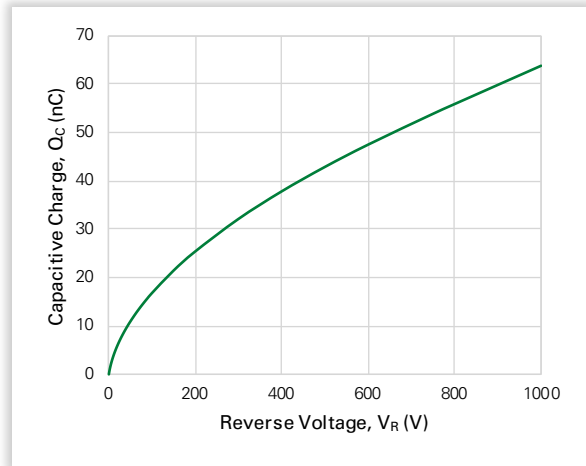


Figure 7. Stored Energy vs. Reverse Voltage

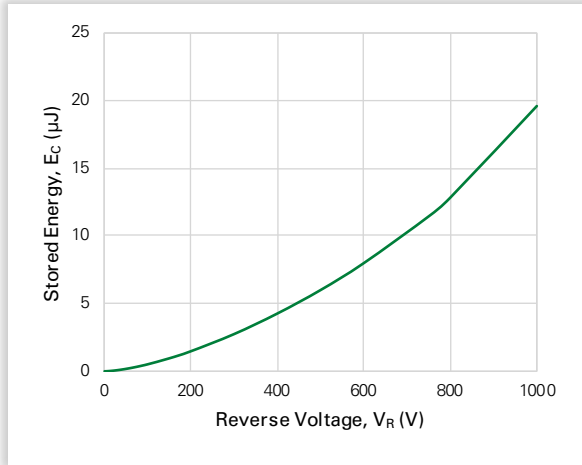
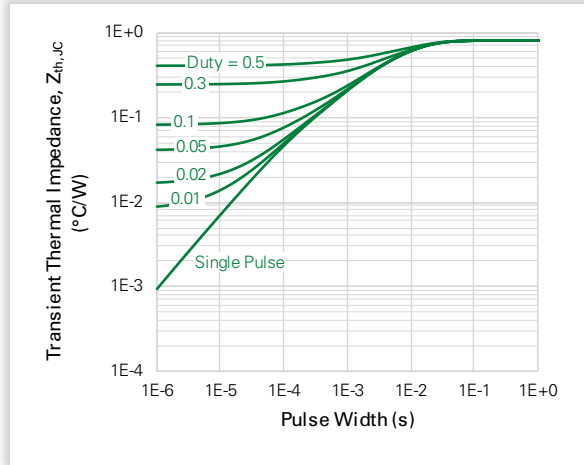
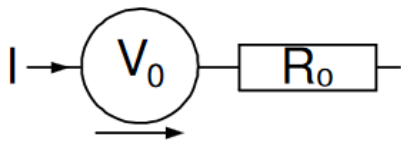


Figure 8. Transient Thermal Impedance



5. V<sub>F</sub> Model for Simulation



$$V_F(T_J) = V_0 + IR_0$$

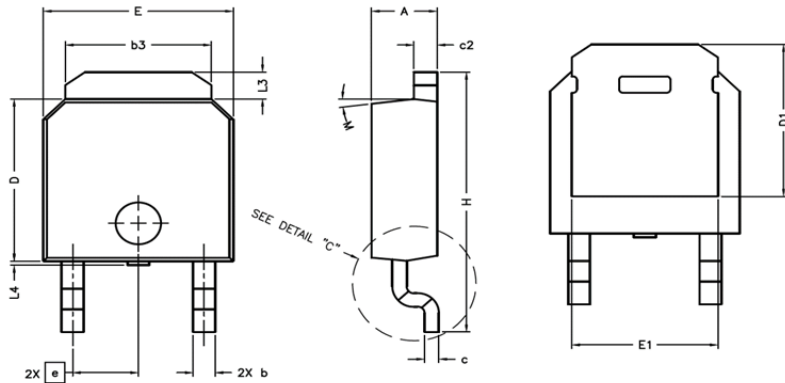
$$V_0 = -1.11 \times 10^{-3} \cdot T_J + 1.01 \times 10^0$$

$$R_0 = 1.61 \times 10^{-6} \cdot T_J^2 + 1.50 \times 10^{-4} \cdot T_J + 4.35 \times 10^{-2}$$

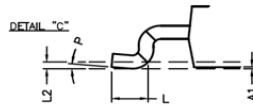
Notes:

- T<sub>J</sub> is junction temperature in °C
- Range valid from 25 °C to 175 °C
- Model represents performance of a typical part

6. Package Dimensions

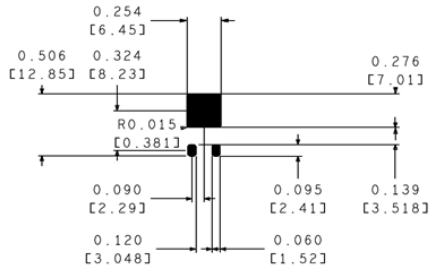


- NOTE:
1. L4 - MAXIMUM PLASTIC PROTRUSION.
  2. L2 - REFERENCE FOR FOOT LENGTH MEASUREMENT.
  3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS B3, L3, D1, AND E1
  4. PACKAGE OUTLINE D AND E EXCLUSIVE OF ANY MOLD FLASHES DIMENSIONS.
  5. PACKAGE OUTLINE D AND E EXCLUSIVE OF ANY BURR DIMENSIONS.
  6. FOR SINGLE-GAUGE LEADFRAME.



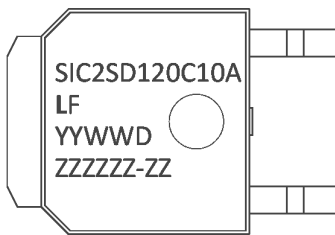
Symbol	Millimeters	
	Min	Max
A	2.159	2.413
A1	-	0.127
b	0.635	1.067
b3	4.953	5.461
c	0.457	0.610
c2	-	0.889
(c2)	0.457	0.610
D	5.969	6.223
D1	5.207	5.715
E	6.350	6.731
E1	4.318	5.207
e	2.29 REF.	
H	9.398	10.414
L	1.016	1.778
L2	0.25 REF.	
L3	0.889	1.270
L4	0.000	0.152
M	15°	
P	-	5°

Recommended Solder Pad Layout



UNIT: Inch [mm]

7. Part Numbering and Marking



- SiC = SiC
- 2 = Gen 2
- SD = Schottky Barrier Diode
- 120 = Voltage Rating (1200 V)
- C = Package (TO-252-2L)
- 10 = Current Rating (10 A)
- A = AEC-Q101 qualified
- YY = Year
- WW = Week
- D = Special Code
- ZZZZZZ-ZZ = Lot Number

8. Packing Options

Part Number	Marking	Packing Mode	M.O.Q.
LSIC2SD120C10A	SIC2SD120C10A	Tape & Reel	2500

